

3/17/04

	L #	Hits	Search Text	DBs
1	L1	86820	(silicon or si or wafer).ti,ab.	USPA T; US-PG PUB
2	L2	10003 4	mold\$4.ti,ab.	USPA T; US-PG PUB
3	L3	1437	1 and 2	USPA T; US-PG PUB
4	L4	36691	etch\$4.ti,ab.	USPA T; US-PG PUB
5	L5	68	3 and 4	USPA T; US-PG PUB
6	L6	10065	(electroplat\$8 or electrodeposit\$8 or electroform\$4 or (electro or electrolytic\$6) adj3 (plat\$4 or deposit\$6 or form\$4)).ti,ab.	USPA T; US-PG PUB
7	L7	86	1 and 4 and 6	USPA T; US-PG PUB
8	L8	83	7 not 5	USPA T; US-PG PUB
9	L9	795	430/320.ccls.	USPA T; US-PG PUB
10	L10	779	216/2.ccls.	USPA T; US-PG PUB
11	L11	282	216/39.ccls.	USPA T; US-PG PUB
12	L12	36	10 and (2 or 6)	USPA T; US-PG PUB
13	L13	6	3 and (9 or 11)	USPA T; US-PG PUB

	L #	Hits	Search Text	DBs
14	L14	84	11 and 1	USPA T; US-PG PUB
15	L15	80	14 not (5 or 7 or 12 or 13)	USPA T; US-PG PUB
16	L17	18	9 and (1 and 4)	USPA T; US-PG PUB
17	L18	32278	((bottom or second or lower) adj surface).ti,ab.	USPA T; US-PG PUB
18	L19	766	1 with 18	USPA T; US-PG PUB
19	L21	44624 3	(conduct\$6 or metal\$4 or gold or chromium).ti,ab.	USPA T; US-PG PUB
20	L22	4128	((other or opposite) adj surface).ti,ab.	USPA T; US-PG PUB
21	L23	107	1 with 22	USPA T; US-PG PUB
22	L24	85055	21 with (layer or film).ti,ab.	USPA T; US-PG PUB
23	L25	151	(19 or 23) and 24	USPA T; US-PG PUB
24	L26	38	4 and 25	USPA T; US-PG PUB
25	L27	92	(deep adj etch\$4 or deepetch\$4 or dem).ti,ab.	USPA T; US-PG PUB
26	L28	7	1 and 27	USPA T; US-PG PUB

	L #	Hits	Search Text	DBs
27	L29	21	chen-di.in.	USPA T; US-PG PUB

3/18/04

	L #	Hits	Search Text	DBs
1	L1	241	205/67.ccls.	USPA T; US-PG PUB
2	L2	197	205/70.ccls.	USPA T; US-PG PUB
3	L3	183	205/135.ccls.	USPA T; US-PG PUB
4	L4	86955	(silicon or si or wafer).ti,ab.	USPA T; US-PG PUB
5	L5	11	(1 or 2 or 3) and 4	USPA T; US-PG PUB
6	L6	9761	etch.ti,ab.	USPA T; US-PG PUB
7	L7	7	(1 or 2 or 3) and 6	USPA T; US-PG PUB
8	L8	14581 80	silicon or si or wafer	EPO; JPO; DERW ENT; IBM_T DB
9	L9	47382 4	(bottom or second or lower or other or opposite) adj (side or surface)	EPO; JPO; DERW ENT; IBM_T DB
10	L10	7054	8 with 9	EPO; JPO; DERW ENT; IBM_T DB
11	L12	68742 4	(conduct\$6 or metal\$4 or gold or chromium) with (layer or film)	EPO; JPO; DERW ENT; IBM_T DB

	L #	Hits	Search Text	DBs
12	L13	898	10 same 12	EPO; JPO; DERW ENT; IBM_T DB
13	L14	24417 4	etch\$4	EPO; JPO; DERW ENT; IBM_T DB
14	L15	230	13 and 14	EPO; JPO; DERW ENT; IBM_T DB
15	L16	24925 40	electroplat\$8 or electrodeposit\$8 or electroform\$4 or (electro or electrolytic) adj3 form\$4 or deposit\$6 or plat\$4	EPO; JPO; DERW ENT; IBM_T DB
16	L17	114	15 and 16	EPO; JPO; DERW ENT; IBM_T DB
17	L18	46999 5	mold\$4	EPO; JPO; DERW ENT; IBM_T DB
18	L22	33994	8 and 18	EPO; JPO; DERW ENT; IBM_T DB
19	L23	6664	8 with 18	EPO; JPO; DERW ENT; IBM_T DB
20	L24	1635	8 near3 18	EPO; JPO; DERW ENT; IBM_T DB

	L #	Hits	Search Text	DBs
21	L25	80	14 and 24	EPO; JPO; DERW ENT; IBM_T DB
22	L26	10071	(conduct\$6 or metal\$4 or gold or chromium) and 22	EPO; JPO; DERW ENT; IBM_T DB
23	L27	2608	(conduct\$6 or metal\$4 or gold or chromium) and 23	EPO; JPO; DERW ENT; IBM_T DB
24	L28	4946	16 and 22	EPO; JPO; DERW ENT; IBM_T DB
25	L29	1053	16 and 23	EPO; JPO; DERW ENT; IBM_T DB
26	L30	269	16 and 24	EPO; JPO; DERW ENT; IBM_T DB
27	L31	10	13 and 18	EPO; JPO; DERW ENT; IBM_T DB
28	L32	4	10 and 14 and 18	EPO; JPO; DERW ENT; IBM_T DB
29	L33	289	deep adj etch\$4 or deepetch\$4	EPO; JPO; DERW ENT; IBM_T DB

	L #	Hits	Search Text	DBs
30	L34	89	8 and 33	EPO; JPO; DERW ENT; IBM_T DB